

# RJK5015DPK

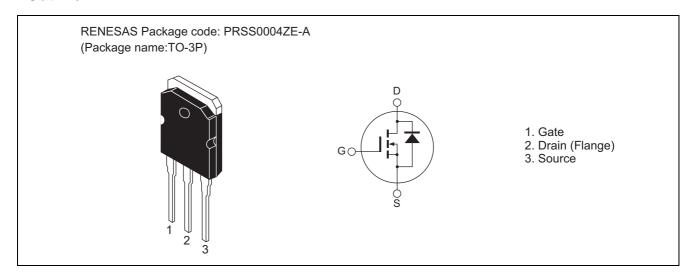
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1360-0200 Rev.2.00 Apr 18, 2007

### **Features**

- Low on-resistance
- Low leakage current
- High speed switching

## **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	500	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	25	А
Drain peak current	I <sub>D (pulse)</sub> Note1	75	А
Body-drain diode reverse drain current	I <sub>DR</sub>	25	А
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	75	А
Avalanche current	I <sub>AP</sub> Note3	7	А
Avalanche energy	E <sub>AR</sub> Note3	2.7	mJ
Channel dissipation	Pch Note2	150	W
Channel to case thermal impedance	θch-c	0.833	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

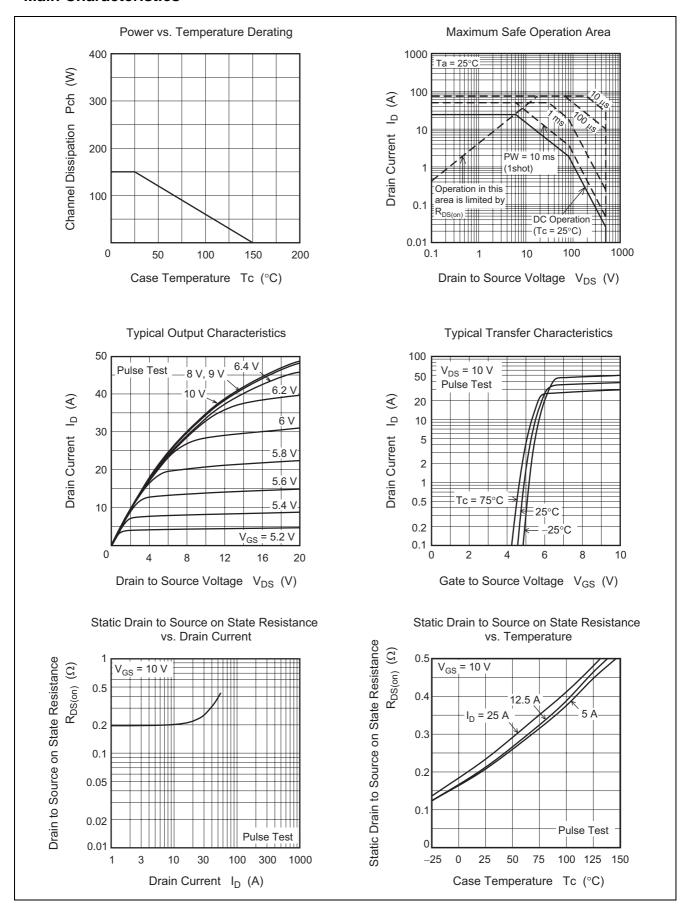
# **Electrical Characteristics**

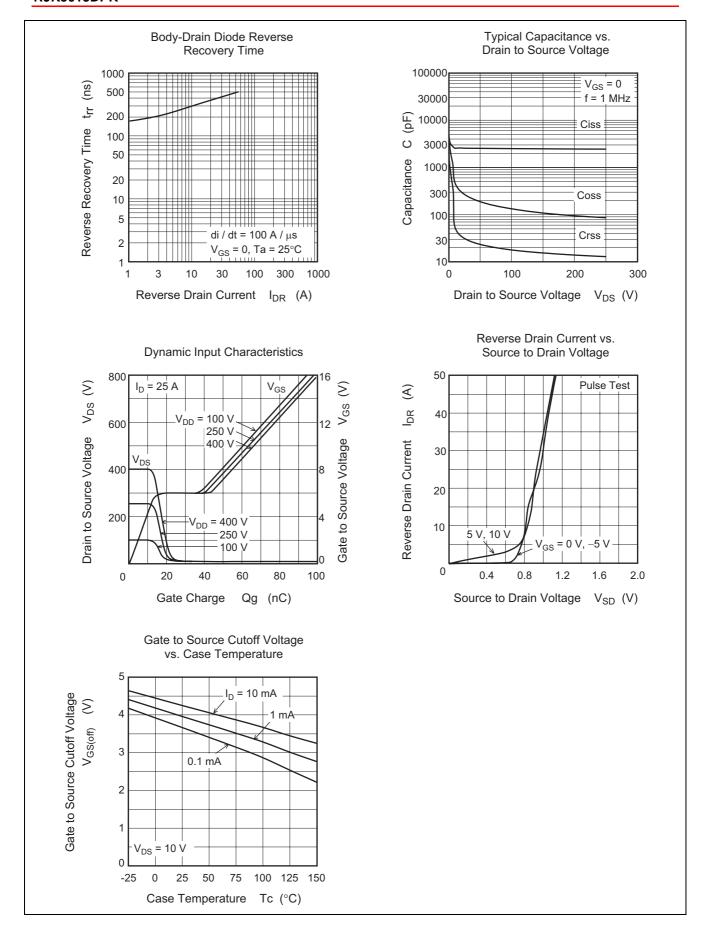
 $(Ta = 25^{\circ}C)$ 

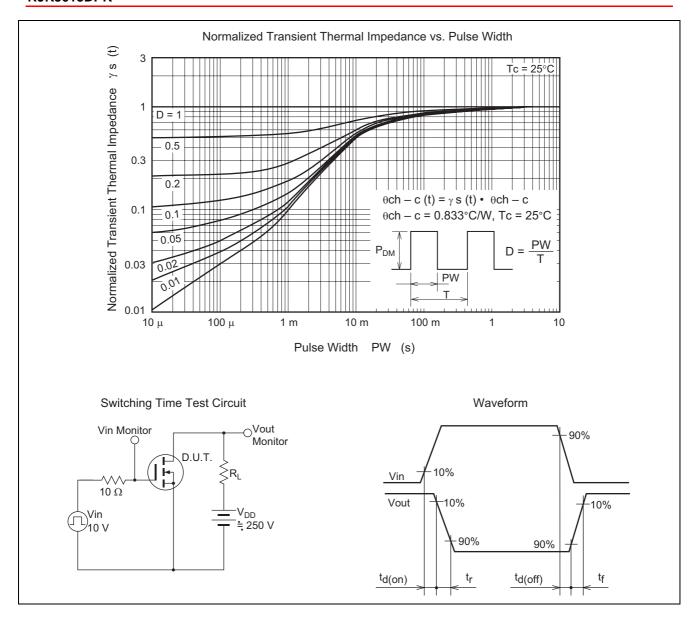
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	0.21	0.24	Ω	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2600	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	270	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss		32	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	42	_	ns	I <sub>D</sub> = 12.5 A
Rise time	t <sub>r</sub>	_	59	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	$t_{d(off)}$	_	103	_	ns	$R_L = 20 \Omega$
Fall time	t <sub>f</sub>	_	45	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	66	_	nC	V <sub>DD</sub> = 400 V
Gate to source charge	Qgs	_	14	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	29	_	nC	I <sub>D</sub> = 25 A
Body-drain diode forward voltage	$V_{DF}$	_	0.96	1.60	V	$I_F = 25 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	trr	_	380	_	ns	$I_F = 25 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

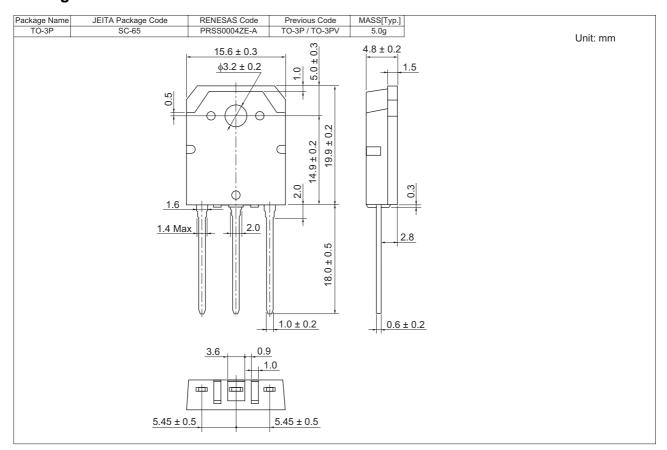
### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK5015DPK-00-T0	360 pcs	Box (Tube)

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